EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1093	438/758.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/16 11:25
L2	1	438/758.ccls. and "HPDCVD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/16 11:26
S1	38	(wafer or semiconductor or substrate) and deposition and (CVD or APCVD or PECVD or HDPCVD) and "thin film" and "deposition system" and gas and (ouput or outlet) and time and rotate and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/16 11:25
S2	1	(wafer or semiconductor or substrate) and deposition and (CVD or APCVD or PECVD or HDPCVD) and "thin film" and "deposition system" and gas and (ouput or outlet) and time and rotate and angle and integer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 09:44
S3	32	(wafer or semiconductor or substrate) and deposition and (CVD or APCVD or PECVD or HDPCVD) and "thin film" and "deposition system" and gas and (ouput or outlet) and time and rotate and angle and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 09:44
S4	18	(wafer or semiconductor or substrate) and deposition and (CVD or APCVD or PECVD or HDPCVD) and "thin film" and "deposition system" and gas and (ouput or outlet) and time and rotate and angle and degree and cycle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 09:46
S5	25	(rotat$4 near8 (wafer or semiconductor or substrate)) and deposition and (CVD or APCVD or PECVD or HDPCVD) and "thin film" and "deposition system" and gas and (ouput or outlet) and time and angle and degree and cycle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 09:47

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S7	8	(rotat$4 near (wafer or semiconductor or substrate)) and deposition and (CVD or APCVD or PECVD or HDPCVD) and "thin film" and "deposition system" and gas and (ouput or outlet) and time and angle and degree and cycle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 09:48
S8	23	(rotat$4 near4 (wafer or semiconductor or substrate)) and deposition and (CVD or APCVD or PECVD or HDPCVD) and "thin film" and "deposition system" and gas and (ouput or outlet) and time and angle and degree and cycle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/09 13:24
S9	21	(semiconductor or substrate or wafer) and ("HDPCVD" or "high density plasma chemical vapor deposition") and "thin film" and rotat$4 and angle and deposit$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 14:15
S10	14	(semiconductor or substrate or wafer) and ("HDPCVD" or "high density plasma chemical vapor deposition") and "thin film" and rotat$4 and angle and deposit$4 and gas and hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 08:51
S11	0	(semiconductor or substrate or wafer) and ("HDPCVD" or "high density plasma chemical vapor deposition") and "thin film" and rotat$4 and angle and deposit$4 and gas and hole and (438/758.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 14:19
S12	0	(semiconductor or substrate or wafer) and ("HDPCVD" or "high density plasma chemical vapor deposition") and "thin film" and rotat$4 and angle and deposit$4 and gas and hole and (438/758.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 09:01
S13	0	(semiconductor or substrate or wafer) and ("HDPCVD" or "high density plasma chemical vapor deposition") and "thin film" and rotat$4 and angle and deposit$4 and gas and hole and (438/758.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 09:01